NSN 5961-01-023-5745

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View Online at https://aerobasegroup.com/nsn/5961-01-023-5745 **Inclosure Material:** Metal **Overall Length:** Between 0.240 inches and 0.260 inches **Terminal Length:** 1.500 inches **Overall Diameter:** Between 0.335 inches and 0.370 inches **Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-5 **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method: Terminal Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 120.0 breakdown voltage, collector-to-base, emitter open and 120.0 breakdown voltage, collector-to-emitter, base open and 4.0 breakdown voltage, emitter-to-base, collector open **Current Rating Per Characteristic:** Between 0.50 amperes source cutoff current and 1.00 amperes source cutoff current **Power Rating Per Characteristic:** 10.0 watts small-signal input power, common-collector absolute **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: pnp **Precious Material And Location:** Eutetic die attachment gold **Precious Material:** Gold **Test Data Document:** 82577-928196 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 3 uninsulated wire lead Shelf Life: N/a

No

Unit Of Measure:

Demilitarization:

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